

FIG. 1

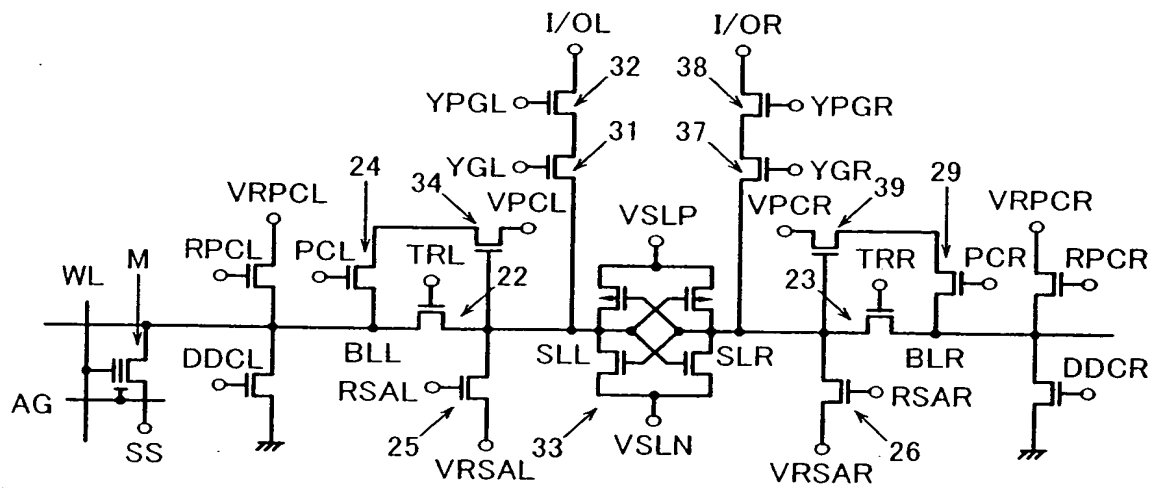


FIG. 2

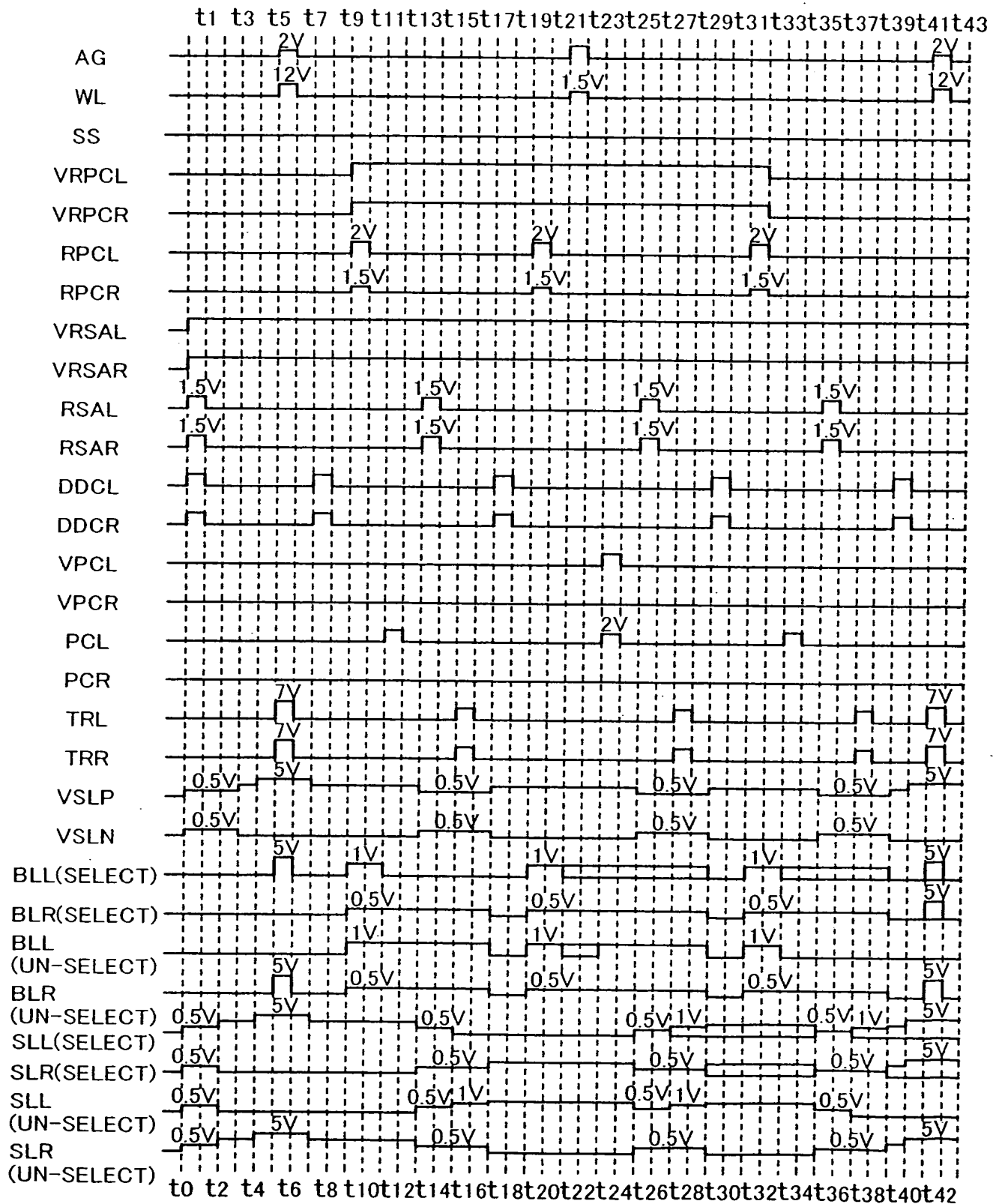


FIG. 3

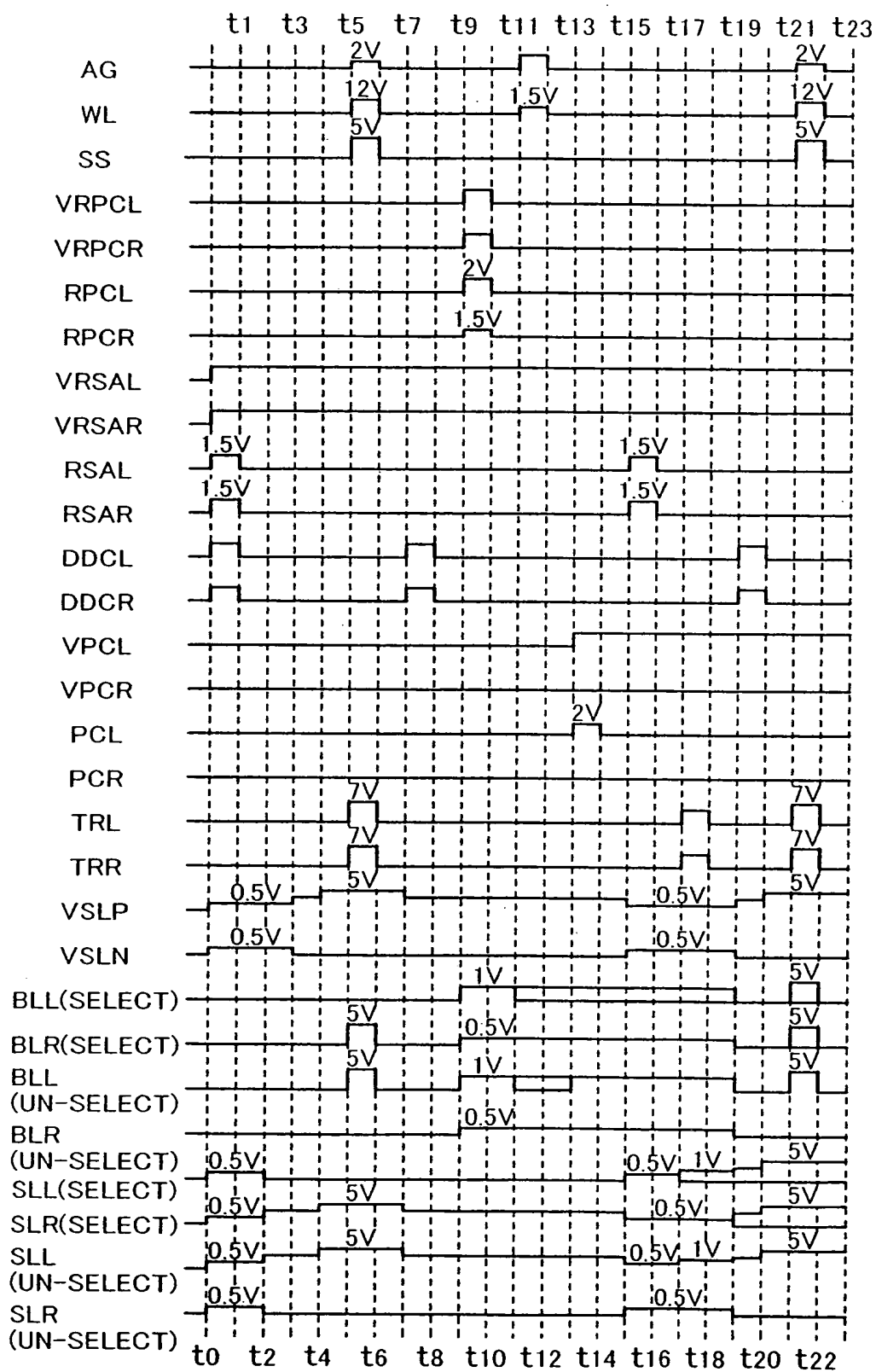


FIG. 4

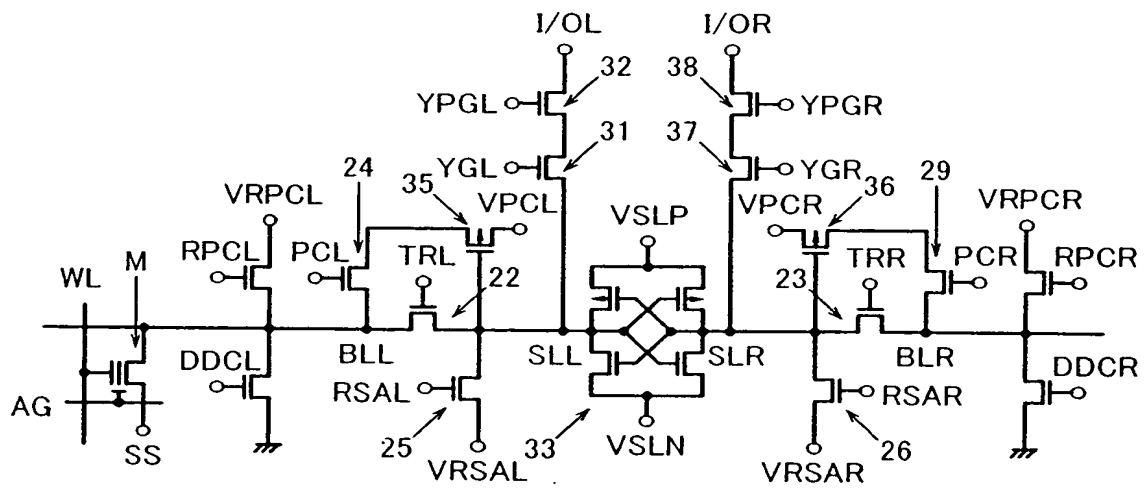


FIG. 5

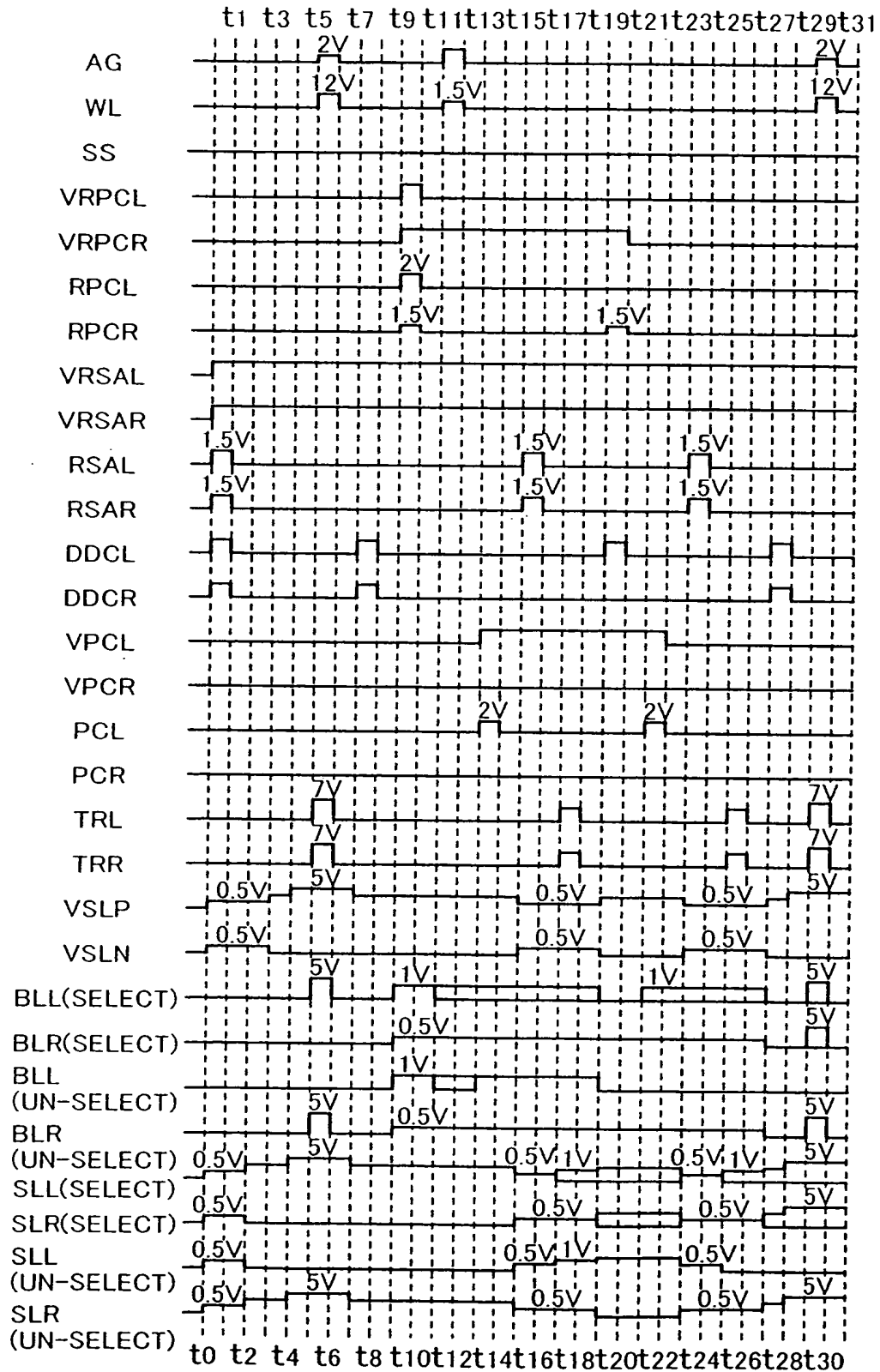


FIG. 6

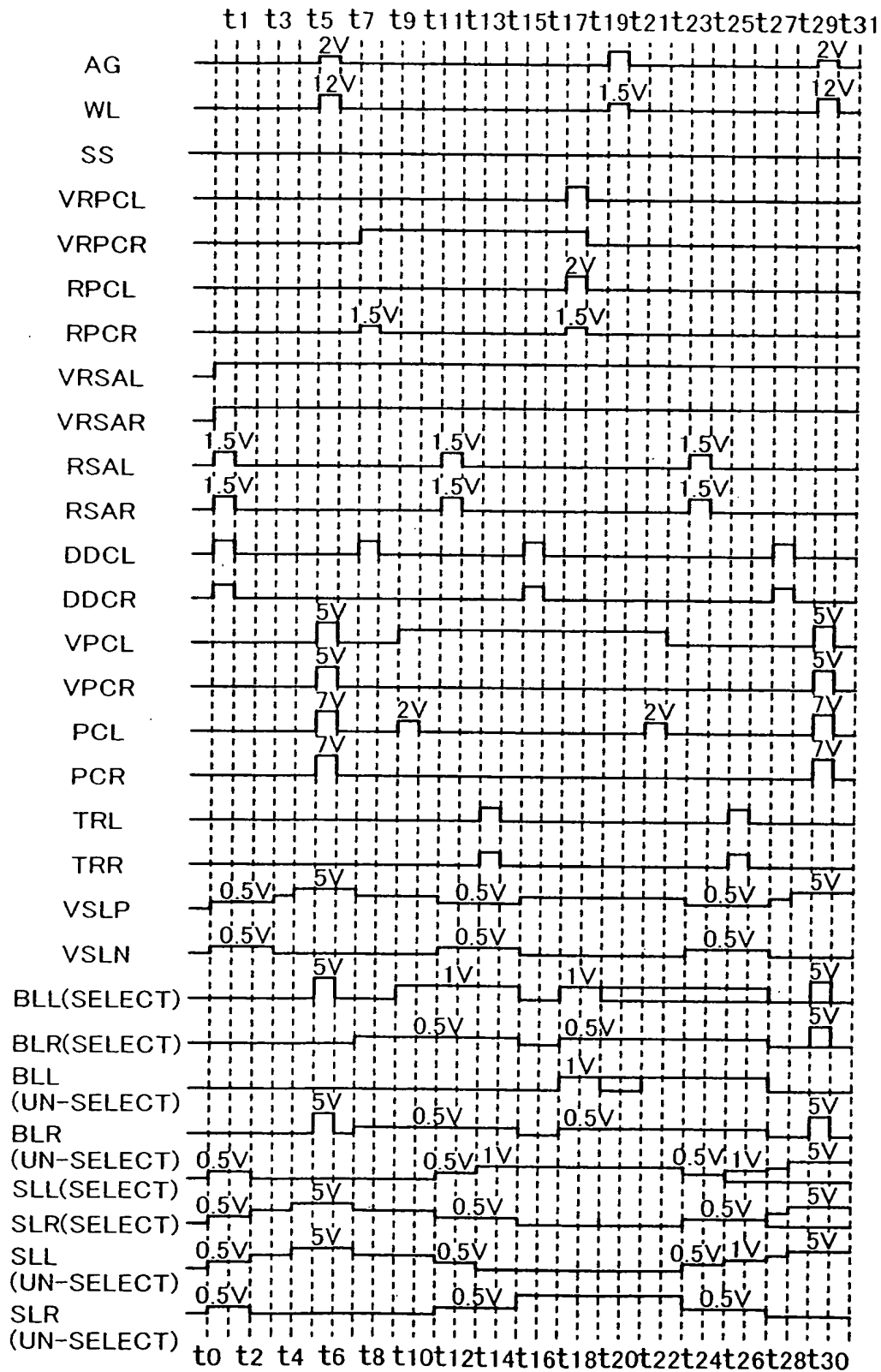


FIG. 7

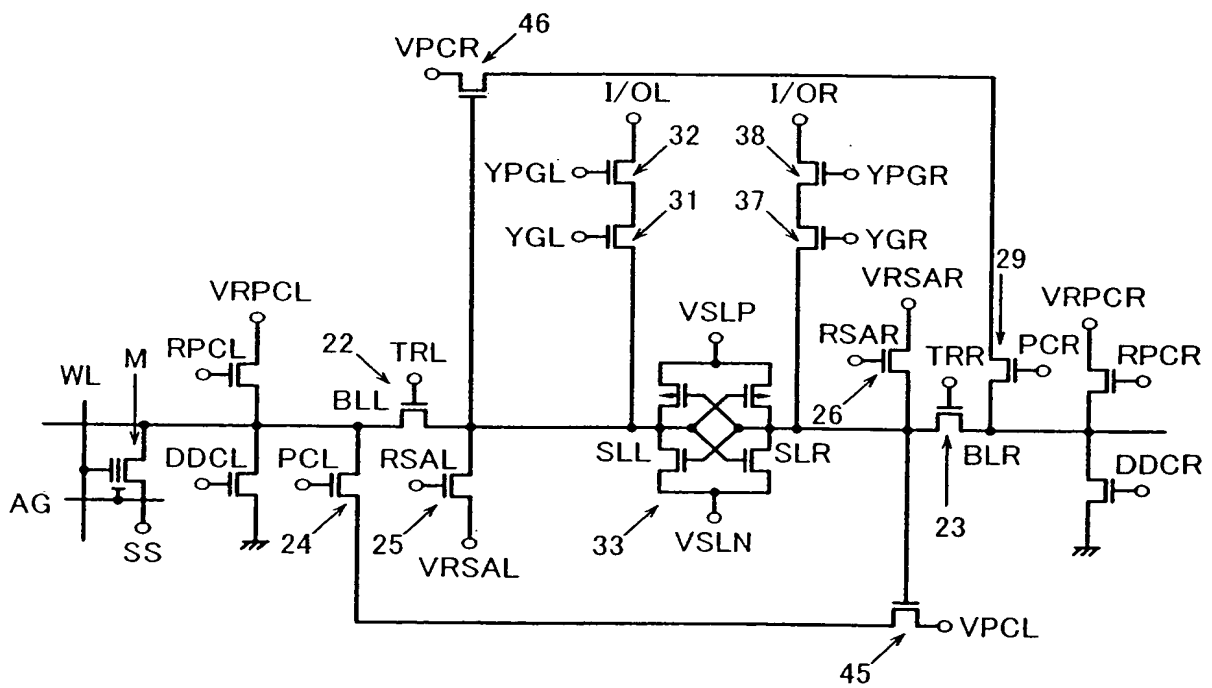


FIG. 8

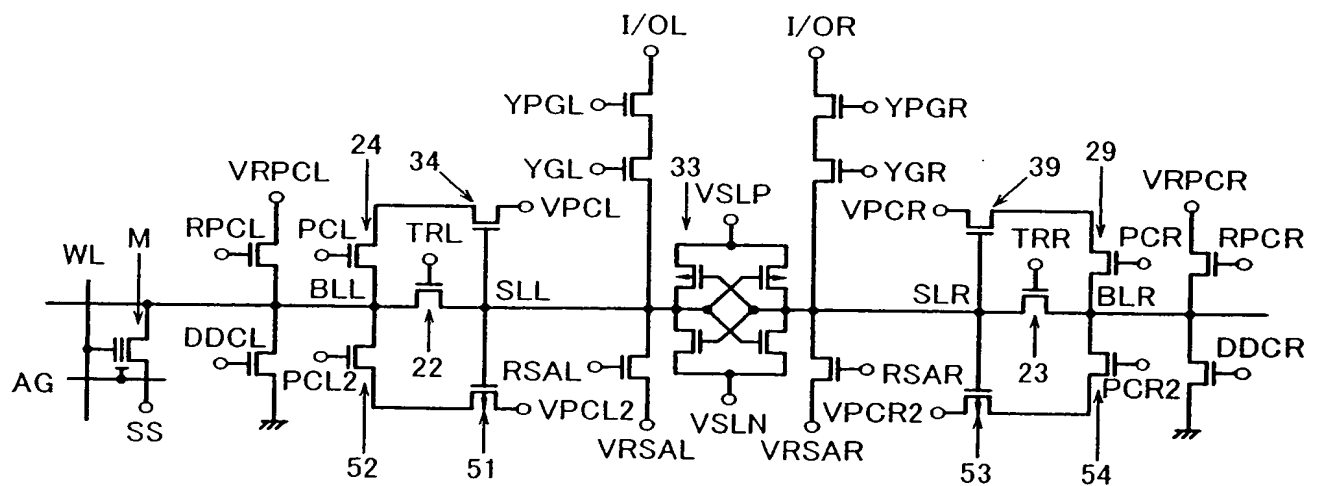


FIG. 9

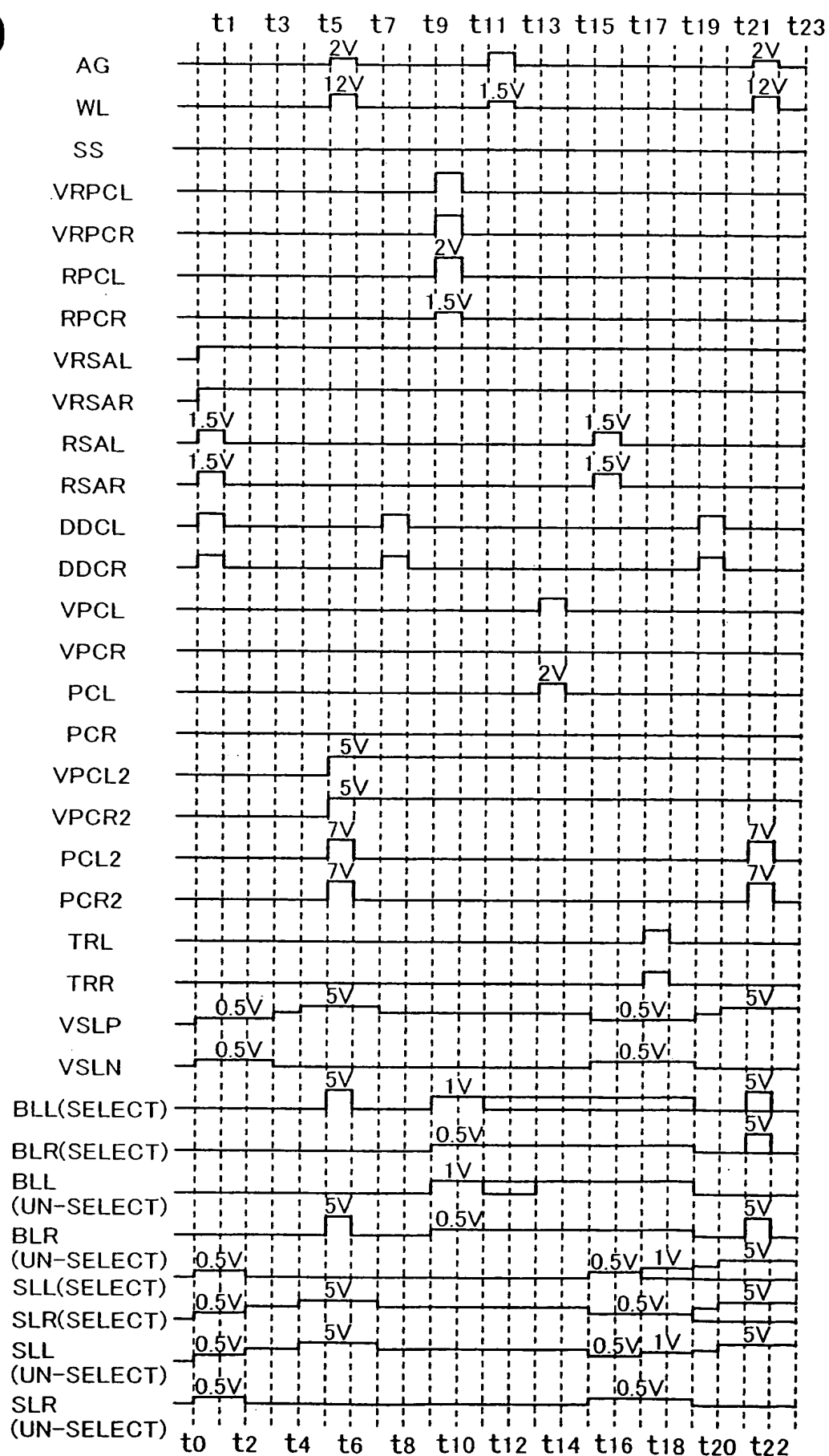


FIG. 10

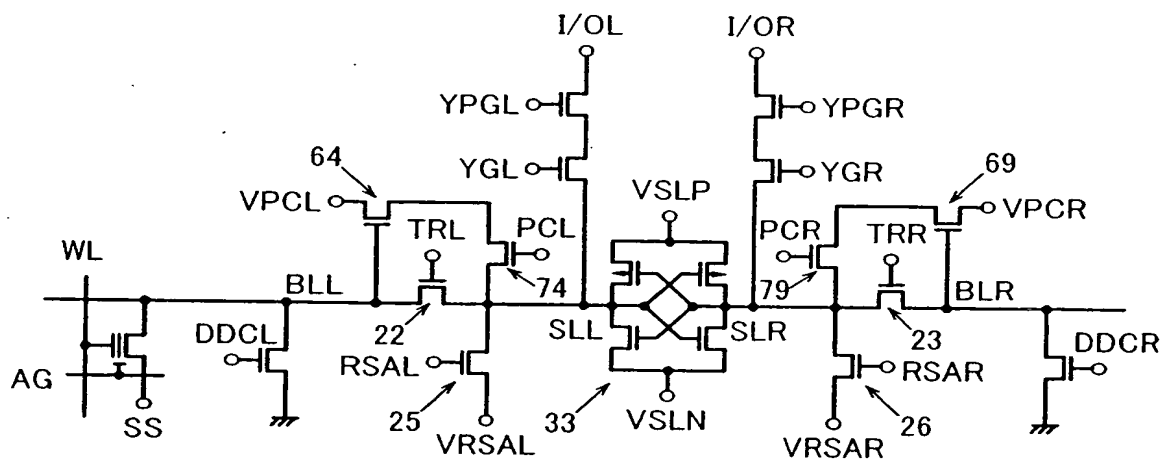


FIG. 11

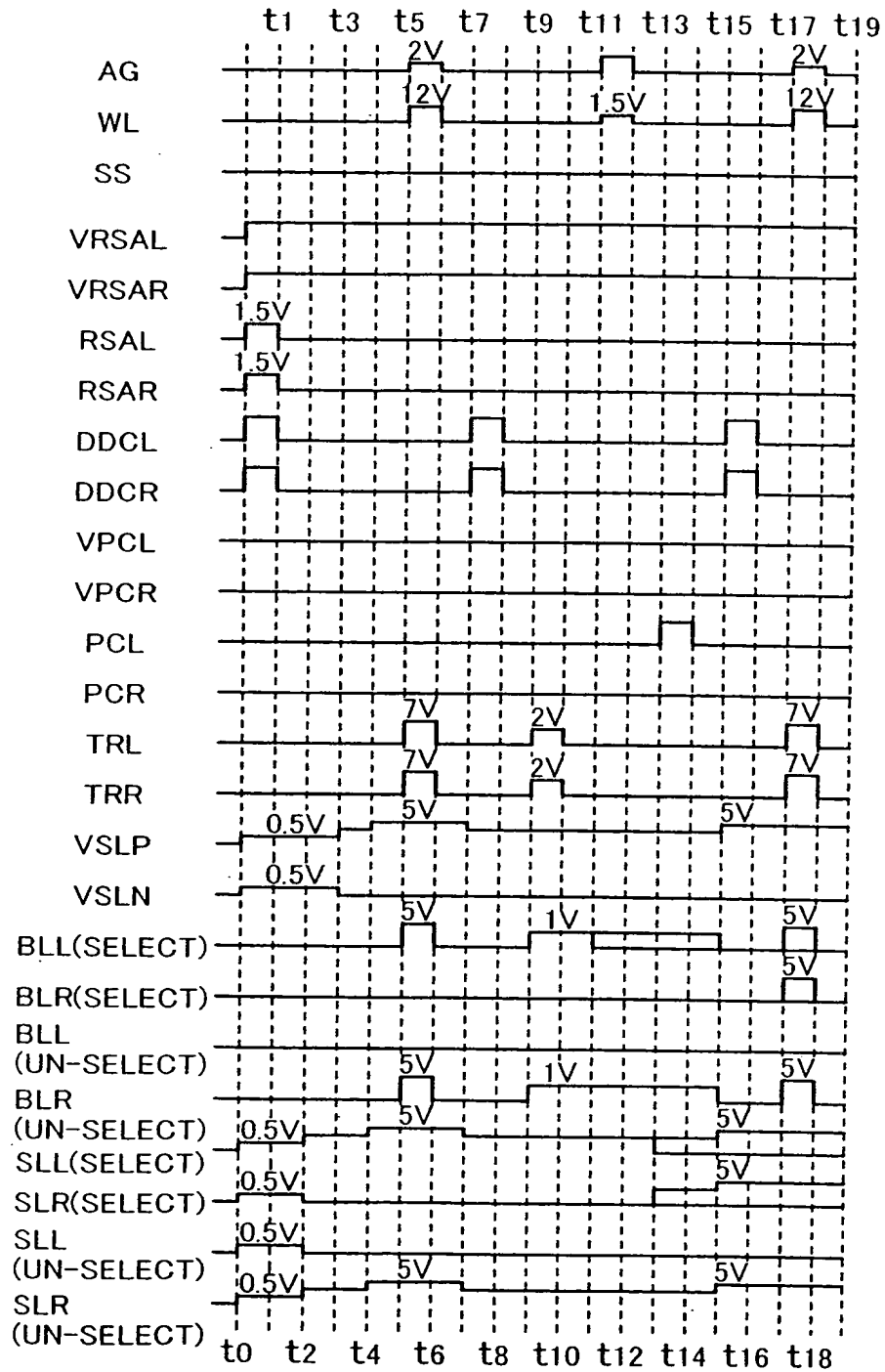


FIG. 12A

PROGRAMMING BIAS
VOLTAGE OF SELECTED
MEMORY CELL

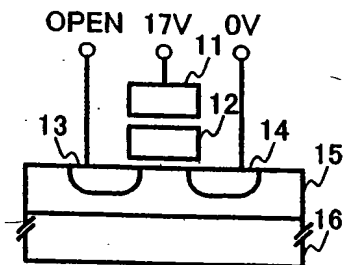


FIG. 12B

PROGRAMMING BIAS
VOLTAGE OF UN-SELECTED
MEMORY CELL

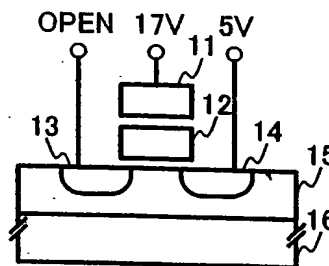


FIG. 13A

CURRENT SENSE AMPLIFIER

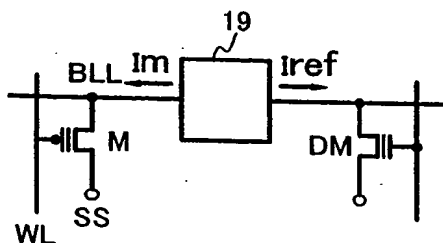


FIG. 13B

VOLTAGE SENSE AMPLIFIER

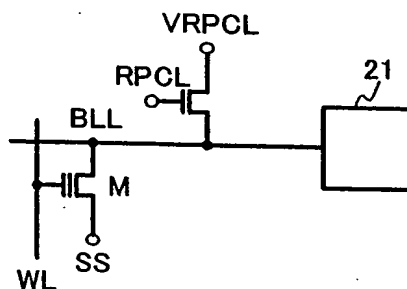


FIG. 14A

PROGRAMMING BIAS
VOLTAGE OF SELECTED
MEMORY CELL

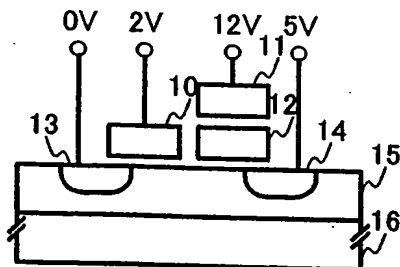


FIG. 14B

PROGRAMMING BIAS
VOLTAGE OF UN-SELECTED
MEMORY CELL

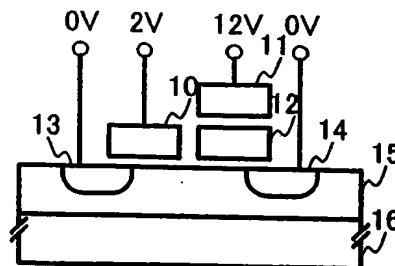


FIG. 15A

CIRCUIT DIAGRAM

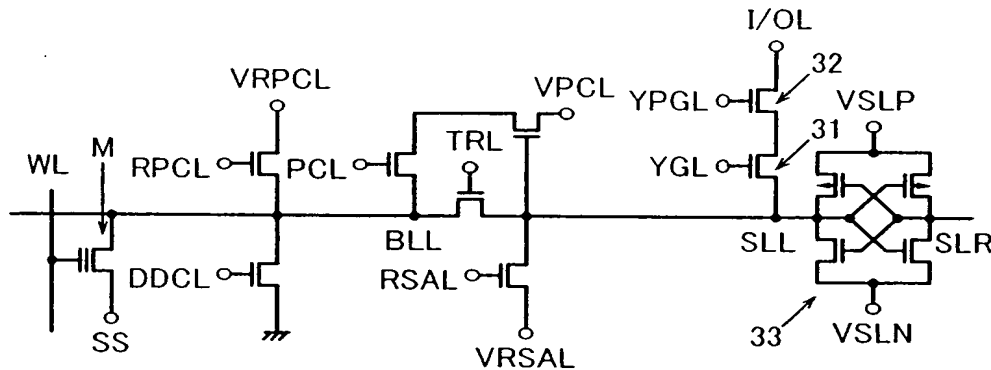


FIG. 15B

FLOW-CHART OF PROGRAMMING/VERIFICATION

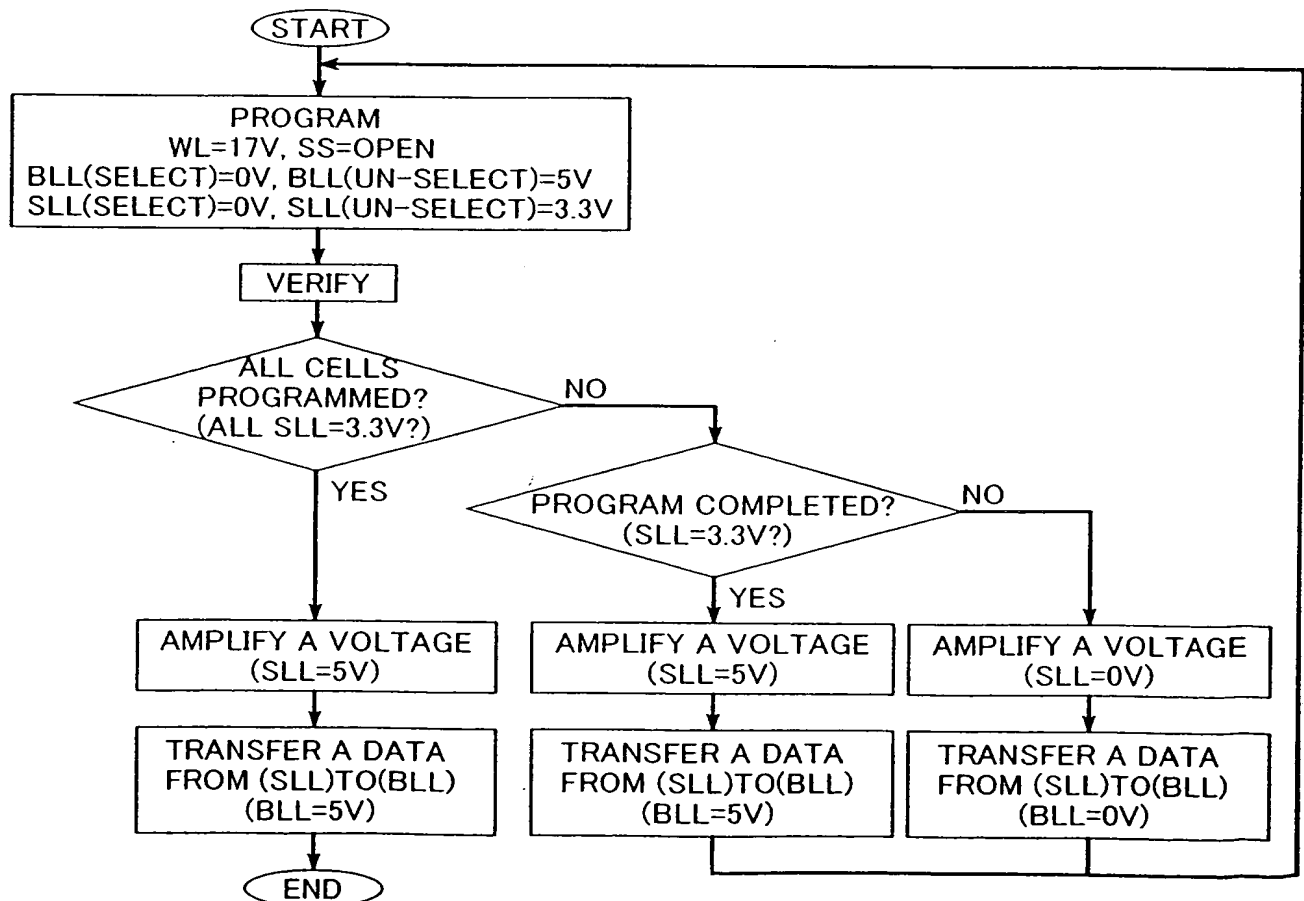


FIG. 16

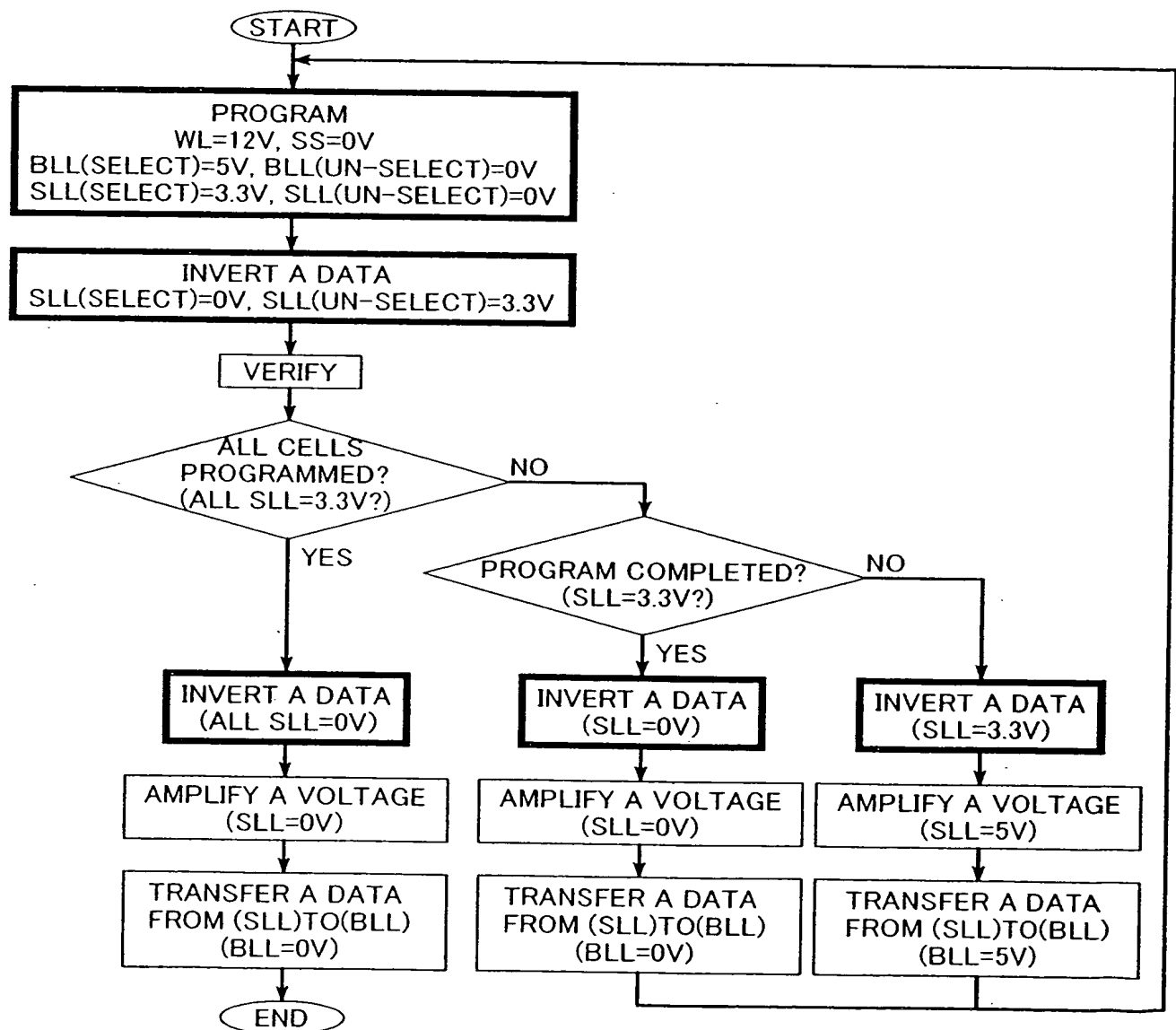


FIG. 17A

TWO-LEVEL STORAGE

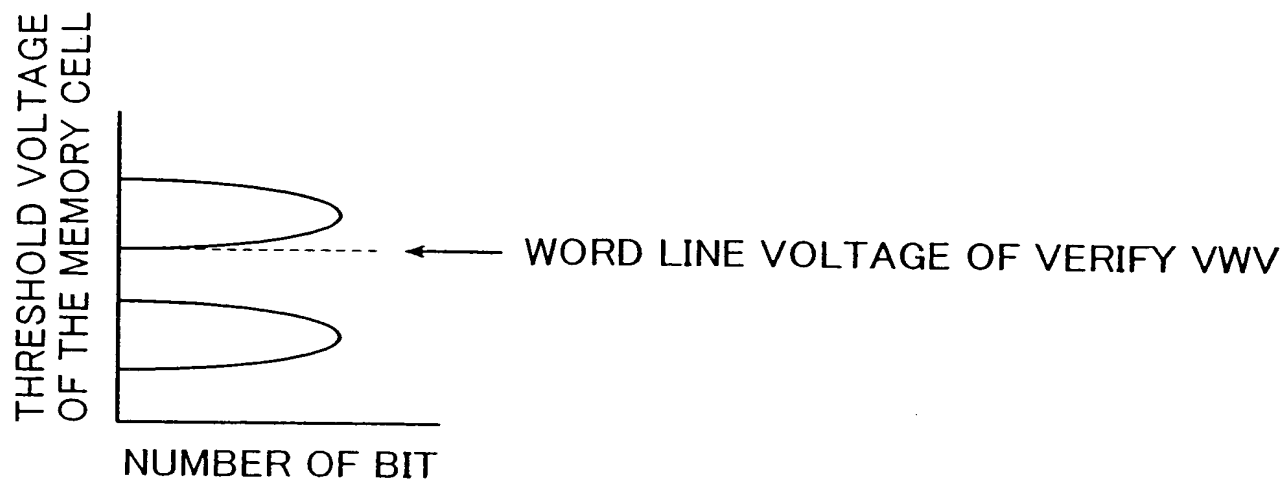


FIG. 17B

MULTI-LEVEL (FOUR-LEVEL) STORAGE

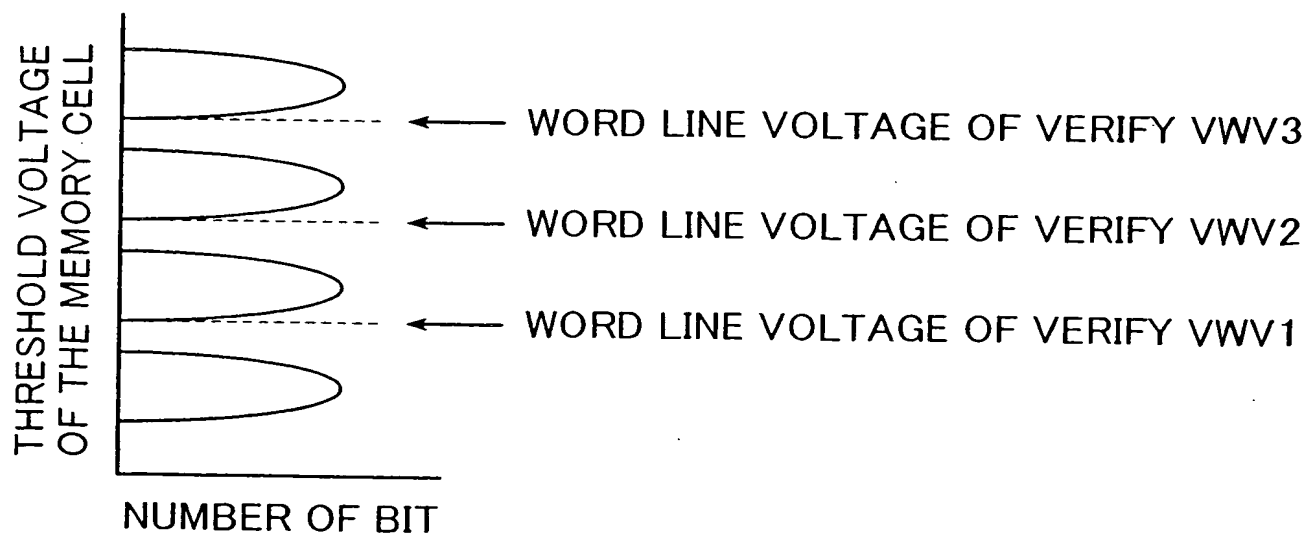


FIG. 18

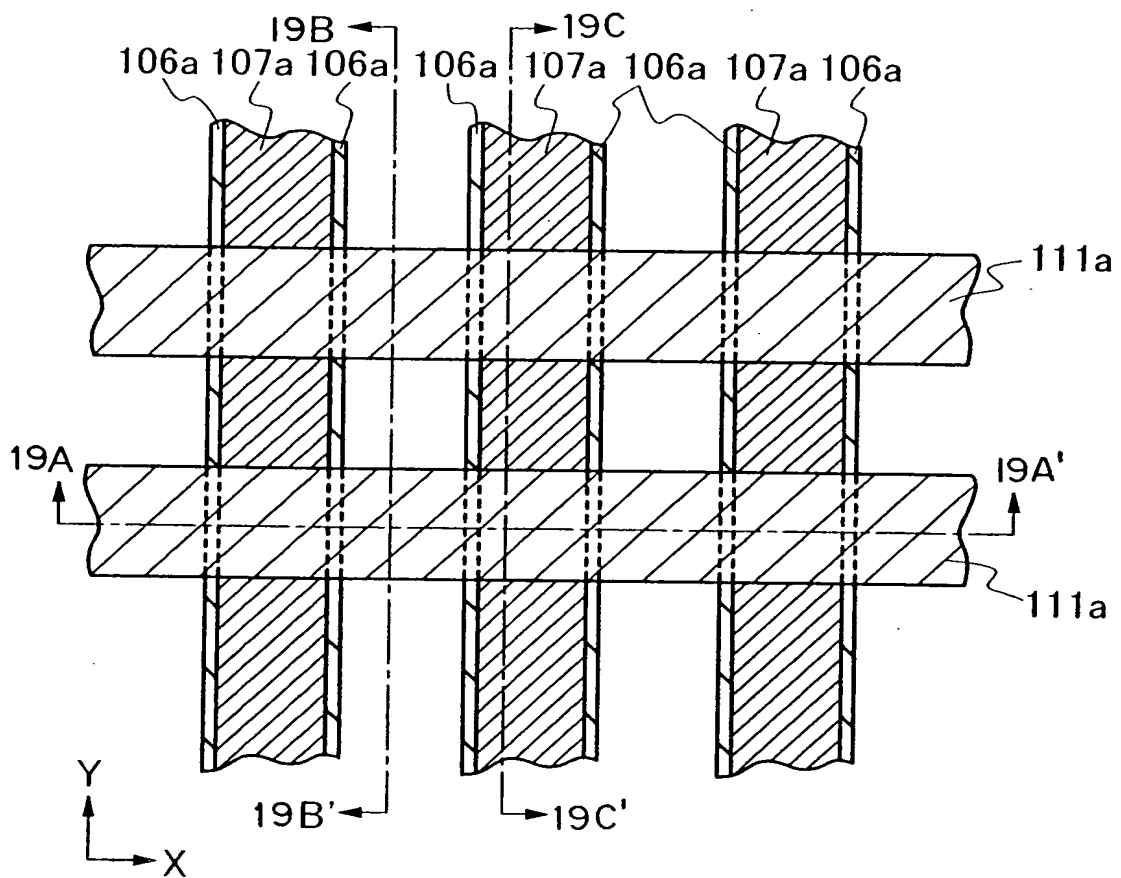


FIG. 19A

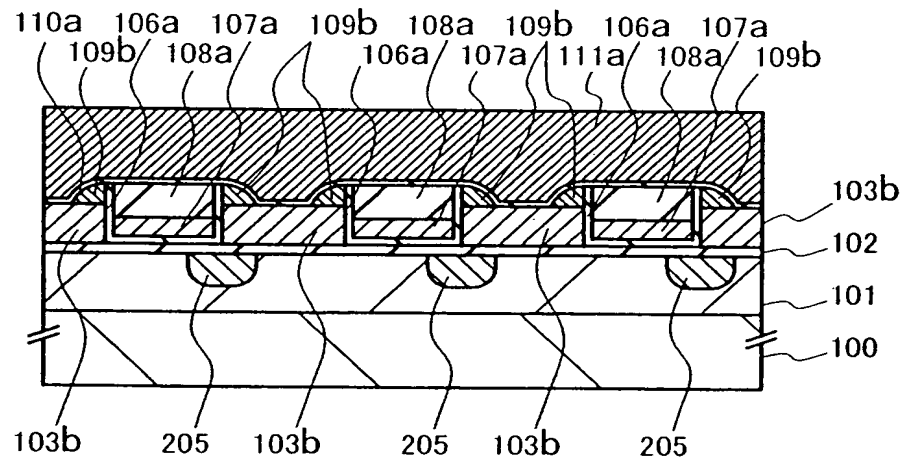


FIG. 19B

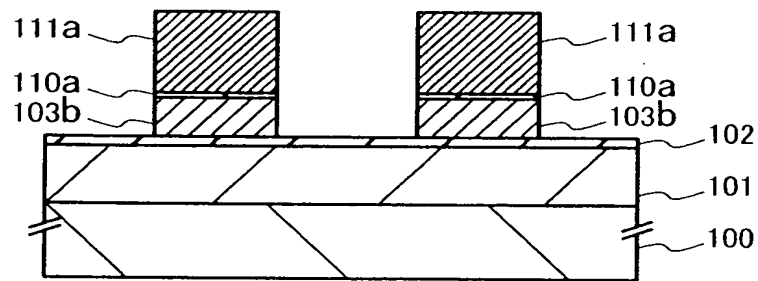


FIG. 19C

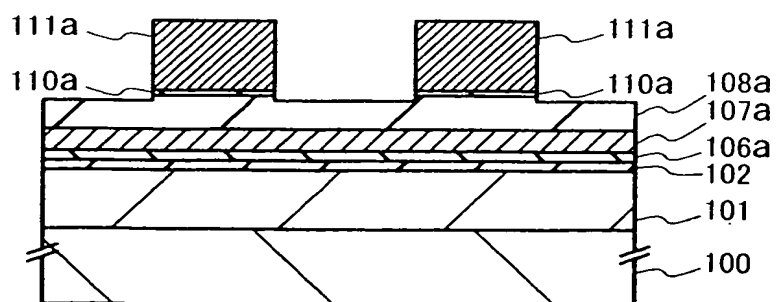


FIG. 20

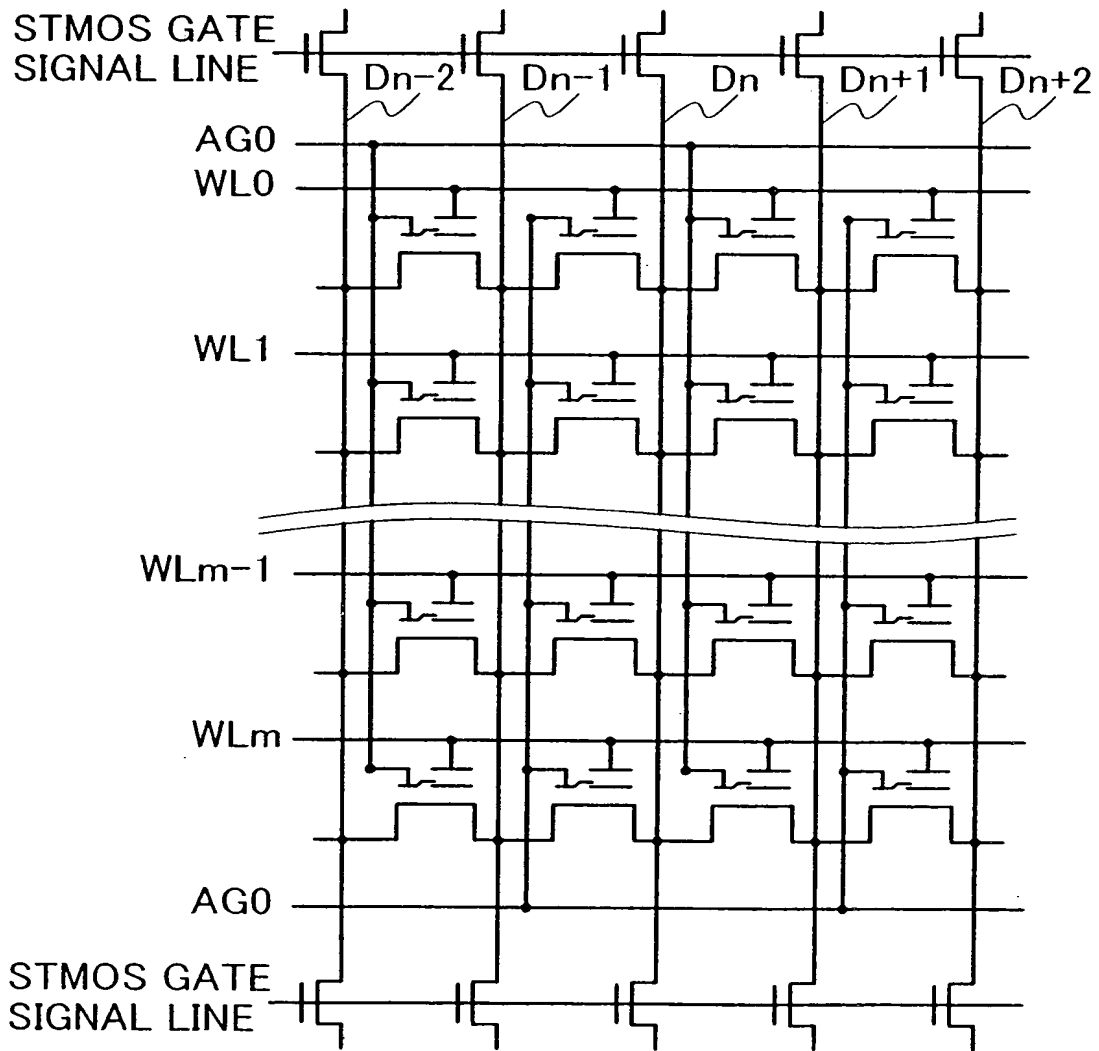


FIG. 21

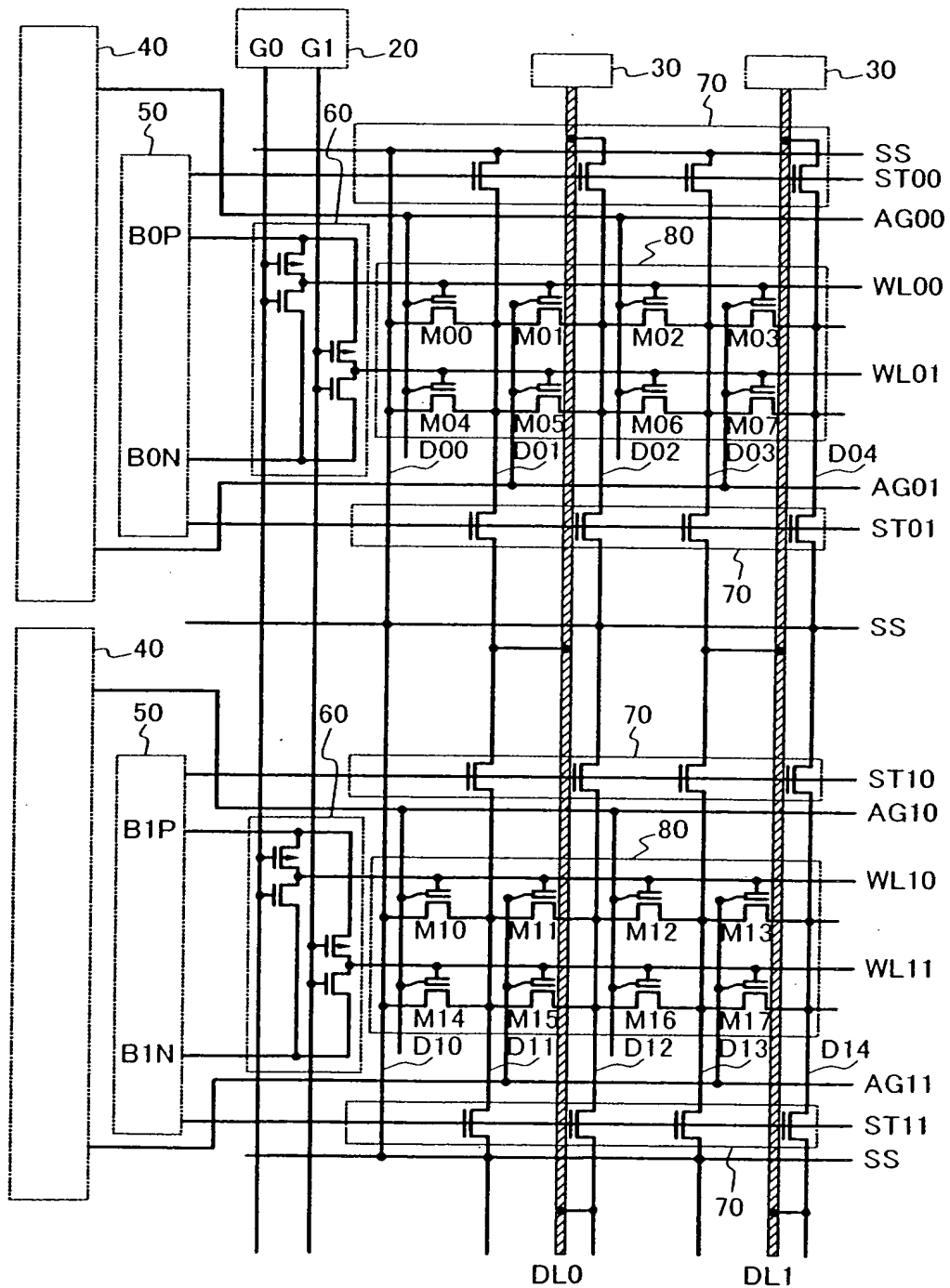


FIG. 22

